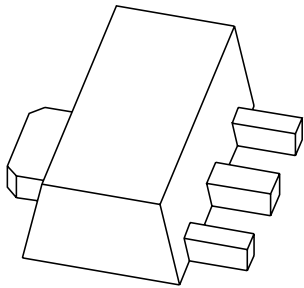


DATA SHEET



BF620; BF622 NPN high-voltage transistors

Product data sheet
Supersedes data of 1999 Apr 21

2004 Dec 14

NPN high-voltage transistors

BF620; BF622

FEATURES

- Low current (max. 50 mA)
- High voltage (max. 300 V).

APPLICATIONS

- Video output stages.

DESCRIPTION

NPN high-voltage transistor in a SOT89 plastic package.
PNP complements: BF621 and BF623.

MARKING

TYPE NUMBER	MARKING CODE
BF620	DC
BF622	DA

PINNING

PIN	DESCRIPTION
1	emitter
2	collector
3	base

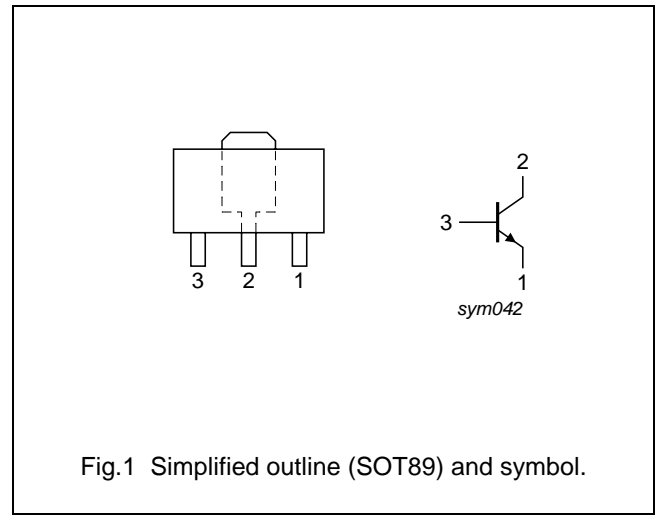


Fig.1 Simplified outline (SOT89) and symbol.

ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
BF620	SC-62	plastic surface mounted package; collector pad for good heat transfer; 3 leads	SOT89
BF622			

NPN high-voltage transistors

BF620; BF622

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

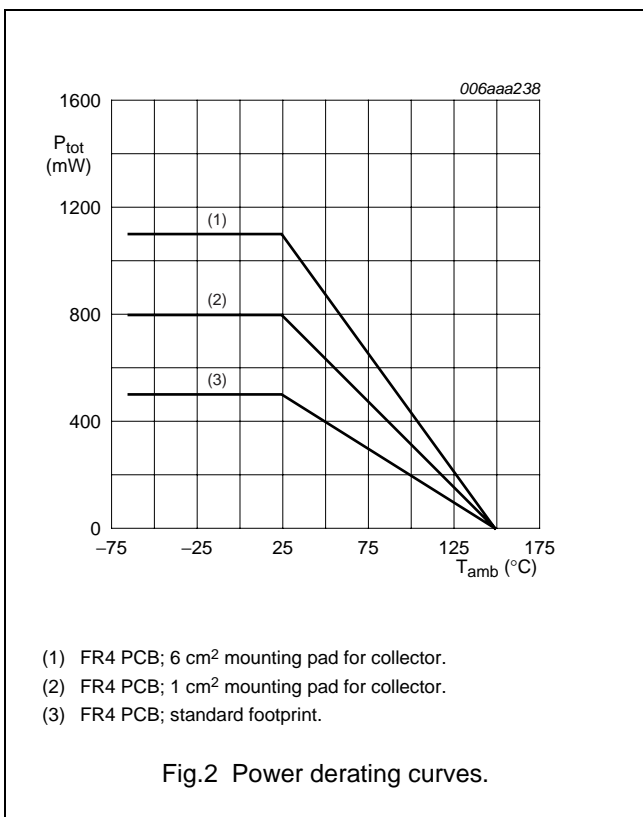
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	BF620		–	300	V
	BF622		–	250	V
V _{CEO}	collector-emitter voltage	open base			
	BF620		–	300	V
	BF622		–	250	V
V _{EBO}	emitter-base voltage	open collector	–	5	V
I _C	collector current (DC)		–	50	mA
I _{CM}	peak collector current		–	100	mA
I _{BM}	peak base current		–	50	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C			
		note 1	–	0.5	W
		note 2	–	0.8	W
		note 3	–	1.1	W
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	ambient temperature		–65	+150	°C

Notes

1. Device mounted on a printed-circuit board, single-sided copper, tin-plated and standard footprint.
2. Device mounted on a printed-circuit board, single-sided copper, tin-plated and mounting pad for collector 1 cm².
3. Device mounted on a printed-circuit board, single-sided copper, tin-plated and mounting pad for collector 6 cm².

NPN high-voltage transistors

BF620; BF622



NPN high-voltage transistors

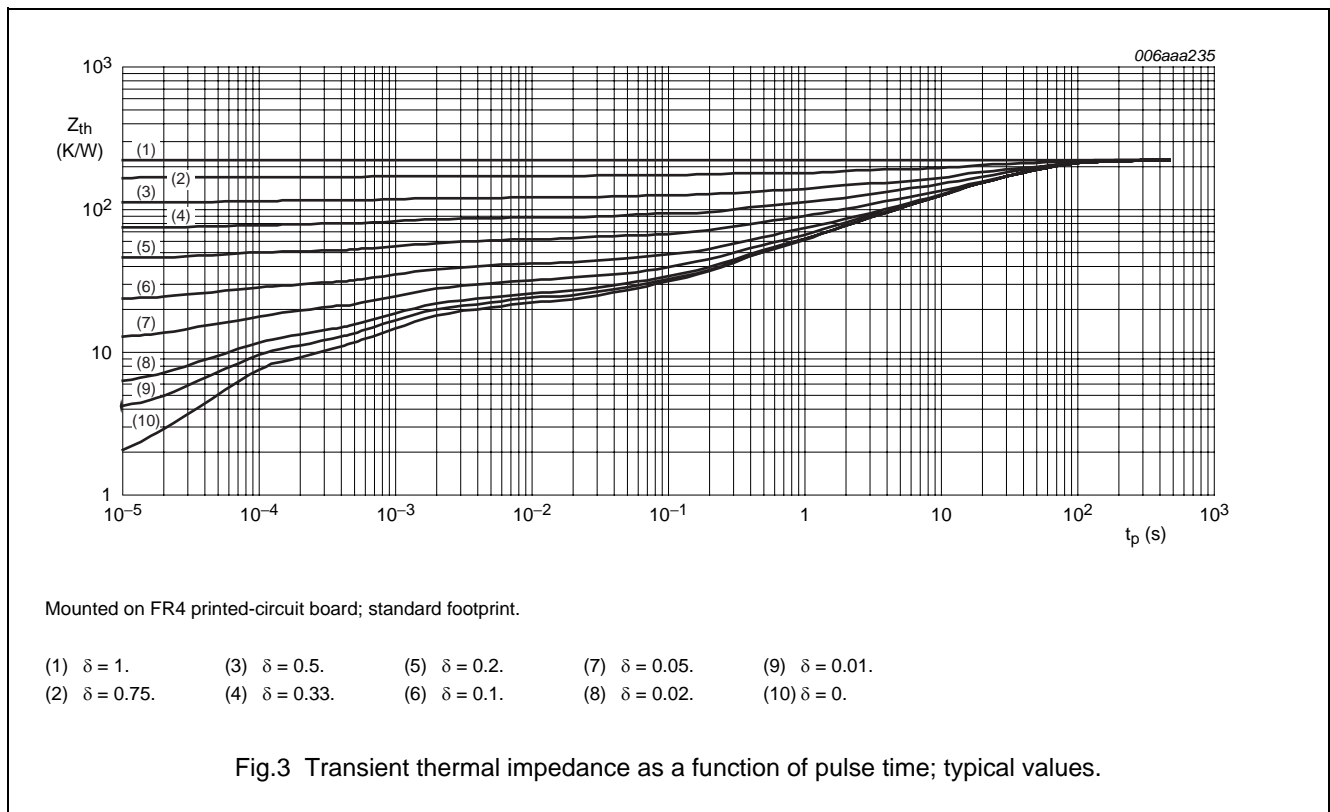
BF620; BF622

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	in free air		
		note 1	250	K/W
		note 2	156	K/W
		note 3	113	K/W
R _{th(j-s)}	thermal resistance from junction to soldering point		30	K/W

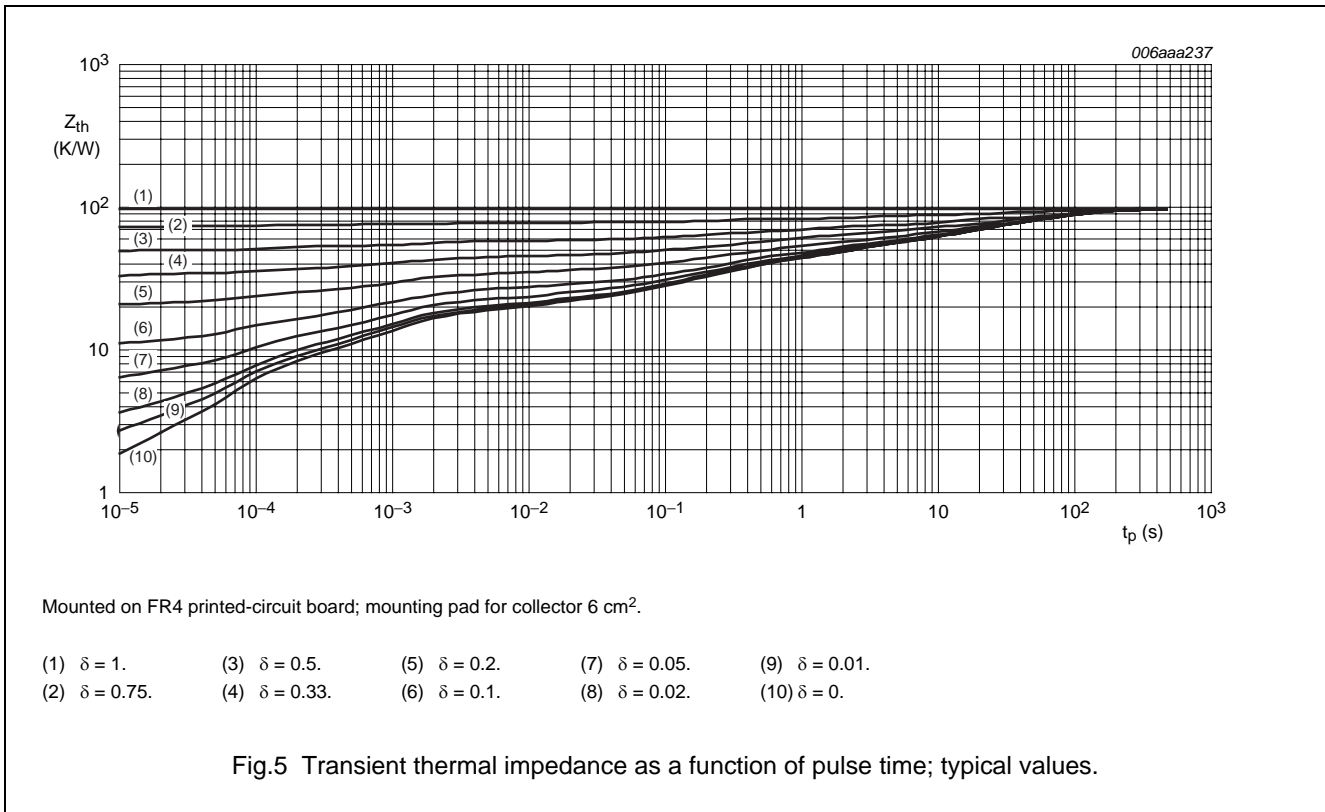
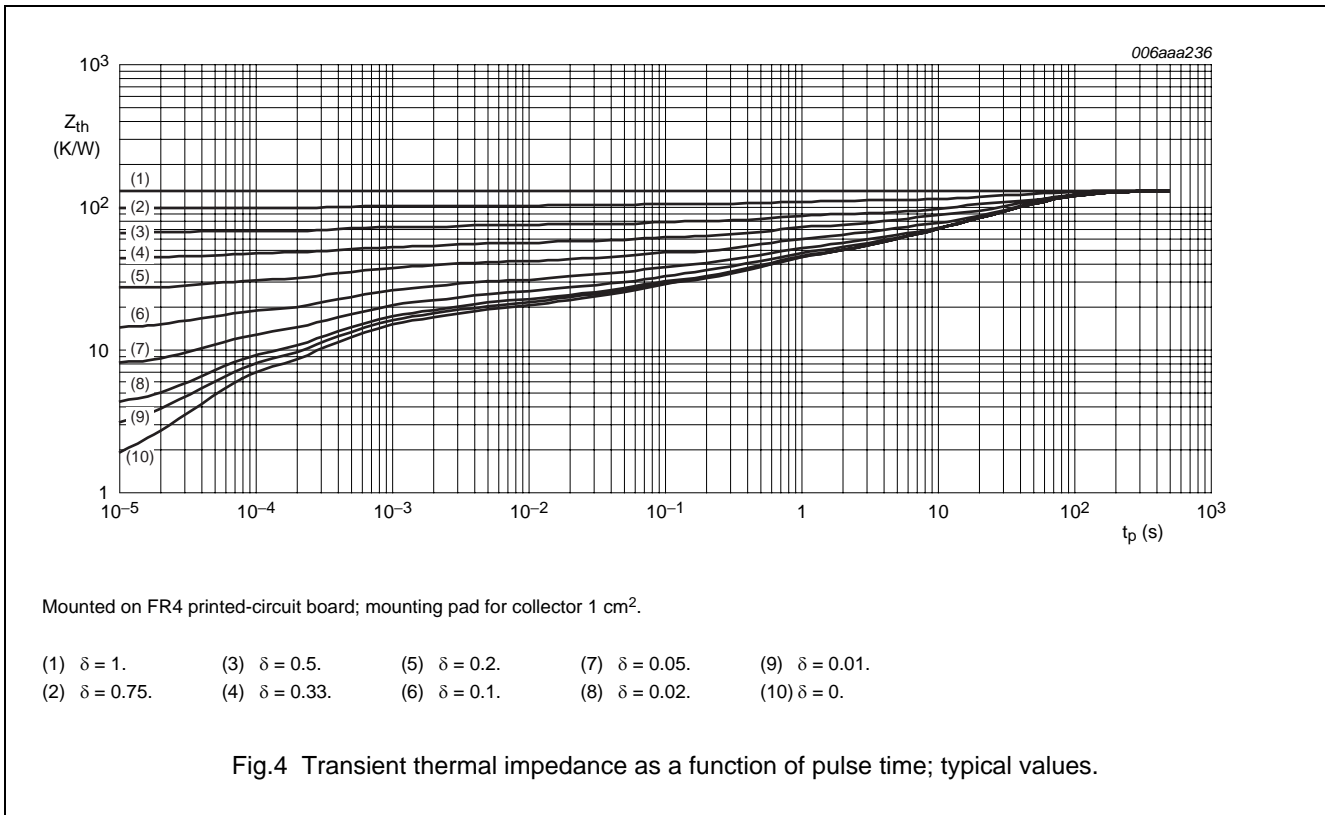
Notes

1. Device mounted on a printed-circuit board, single-sided copper, tin-plated and standard footprint.
2. Device mounted on a printed-circuit board, single-sided copper, tin-plated and mounting pad for collector 1 cm².
3. Device mounted on a printed-circuit board, single-sided copper, tin-plated and mounting pad for collector 6 cm².



NPN high-voltage transistors

BF620; BF622



NPN high-voltage transistors

BF620; BF622

CHARACTERISTICS $T_{amb} = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	$I_E = 0\text{ A}; V_{CB} = 200\text{ V}$	–	10	nA
		$I_E = 0\text{ A}; V_{CB} = 200\text{ V}; T_j = 150\text{ °C}$	–	10	μA
I_{EBO}	emitter-base cut-off current	$I_C = 0\text{ A}; V_{EB} = 5\text{ V}$	–	50	nA
h_{FE}	DC current gain	$I_C = 25\text{ mA}; V_{CE} = 20\text{ V}$	50	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 30\text{ mA}; I_B = 5\text{ mA}$	–	600	mV
C_{re}	feedback capacitance	$I_C = i_c = 0\text{ A}; V_{CE} = 30\text{ V}; f = 1\text{ MHz}$	–	1.6	pF
f_T	transition frequency	$I_C = -10\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$	60	–	MHz

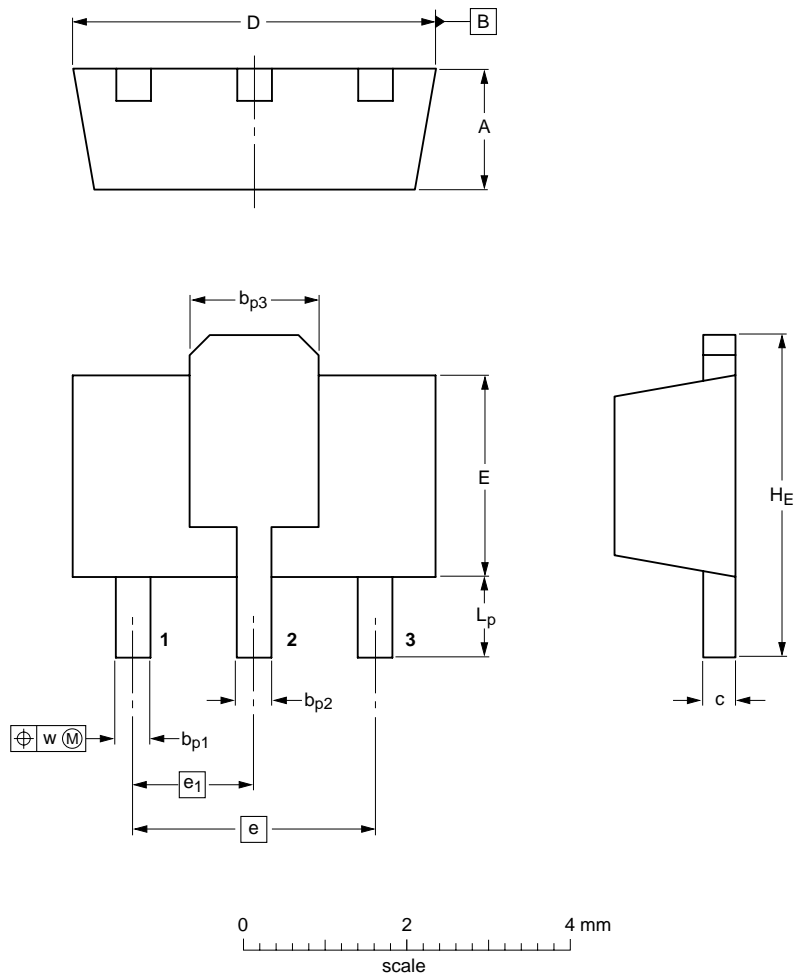
NPN high-voltage transistors

BF620; BF622

PACKAGE OUTLINE

Plastic surface-mounted package; collector pad for good heat transfer; 3 leads

SOT89



DIMENSIONS (mm are the original dimensions)

UNIT	A	b _{p1}	b _{p2}	b _{p3}	c	D	E	e	e ₁	H _E	L _p	w
mm	1.6 1.4	0.48 0.35	0.53 0.40	1.8 1.4	0.44 0.23	4.6 4.4	2.6 2.4	3.0	1.5	4.25 3.75	1.2 0.8	0.13

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT89		TO-243	SC-62		04-08-03 06-03-16